

SNV/U High Performances UV Microchip Series



KEY FEATURES

- 355 nm and 266 nm
- Repetition rate up to 30 kHz
- Ultrashort pulses down to 550 ps
- Multi-kW peak power
- Excellent beam quality
- Efficient, air-cooled
- Sealed package, extremely long life

For generating high peak power ultraviolet pulses of a few hundred picoseconds, microchip lasers are economical, compact, and reliable. Micro-joule UV pulses are generated by harmonic conversion of the IR passively Q-switched Nd:YAG engine. Microchips are also easy to operate and service ; controllers can be used with every laser head model and swapped within minutes while conserving constant performances. The SNV and SNU series are designed for high average power, delivering multi-kW peak power at repetition rates up to 30 kHz.

APPLICATIONS

- Semiconductor inspection
- Laser-induced fluorescence (LIF)
- Micro dissection
- Organic compound marking and micromachining
- Biohazard detection
- Time resolved fluorescence
- Laser Induced Breakdown Spectroscopy (LIBS)
- Biophotonics

TECHNICAL SPECIFICATIONS

New!

	SNV-05P-100	SNV-20F-100 ⁽⁷⁾	SNV-40P-100	SNV-60P-100	SNU-02P-100	SNU-20F-100
Wavelength	355nm	355nm	355nm	355nm	266nm	266nm
Repetition Rate	>5kHz	>19kHz	>19kHz	>29kHz	>6kHz	>19kHz
Pulse duration (FWHM)⁽¹⁾	<0.6ns	<0.6ns	<0.6ns	<0.6ns	<0.6ns	<0.6ns
Output power⁽²⁾	>5mW	>10mW	>40mW	>58mW	>2mW	>10mW
Output energy	>0.5μJ	>0.5μJ	>2μJ	>2μJ	>0.3μJ	>0.5μJ
Peak Power	>0.7kW	0.7kW	> 5 kW	> 5 kW	>0.5kW	>0.7kW
Short term (1min) power stability⁽³⁾	<±2%	<±2%	<±2%	<±2%	<±2%	<±2%
Long term (6 hrs) power stability⁽³⁾	<±5%	<±5%	<±5%	<±5%	<±5%	<±5%
Beam profile	Gaussian TEM00	Gaussian TEM00	Gaussian TEM00	Gaussian TEM00	See note (5)	See note (5)
Full angle divergence						
Horizontal@1/e²	8.5±2mrad	11±2mrad	11±2mrad	11±2mrad	11±2mrad	11.5±2mrad
Vertical@1/e²	6±2mrad	7±2mrad	7±2mrad	7±2mrad	<1.5mm ⁽⁶⁾	0.65±0.25mrad
M²⁽⁴⁾	<1.3	<1.3	<1.3	<1.3	<1.3	<1.4
Gaussian fit in far field	N/A	N/A	N/A	N/A	N/A	>85%
Polarization	Linear PER>20dB	Linear PER>20dB	Linear PER>20dB	Linear PER>20dB	Linear PER>20dB	Linear PER>20dB
Package dimensions	180x55x36mm	186x60x36mm	186x60x36mm	186x60x36mm	180x55x36mm	210x60x36mm
Package weight	400g	500g	500g	500g	400g	500g
Options (table p3)	C	C	C	C	C	C
Options included	-	S	S	S	-	S

NOTES

- (1) Measured with 1GHz photodiode and 1GHz/10GS/s oscilloscope.
- (2) Measurement performed with an OPHIR thermal power sensor (OPHIR 3A-FS-SH)
- (3) For temperature variation < ± 3°C and < 3°C/hour, stability is measured with calorimeter - detector band [DC, 2Hz]
- (4) Mean average value $M = \sqrt{XY}$, X and Y being respectively the major and minor axis of the ellipse
- (5) Beam exhibits different profile in horizontal (Gaussian) and vertical ((sin x /x)² in far-field) plan
- (6) 5%/95% diameter, at 300mm from laser output
- (7) Contact factory for availability

COMPLEMENTARY INFORMATION & OPTIONS

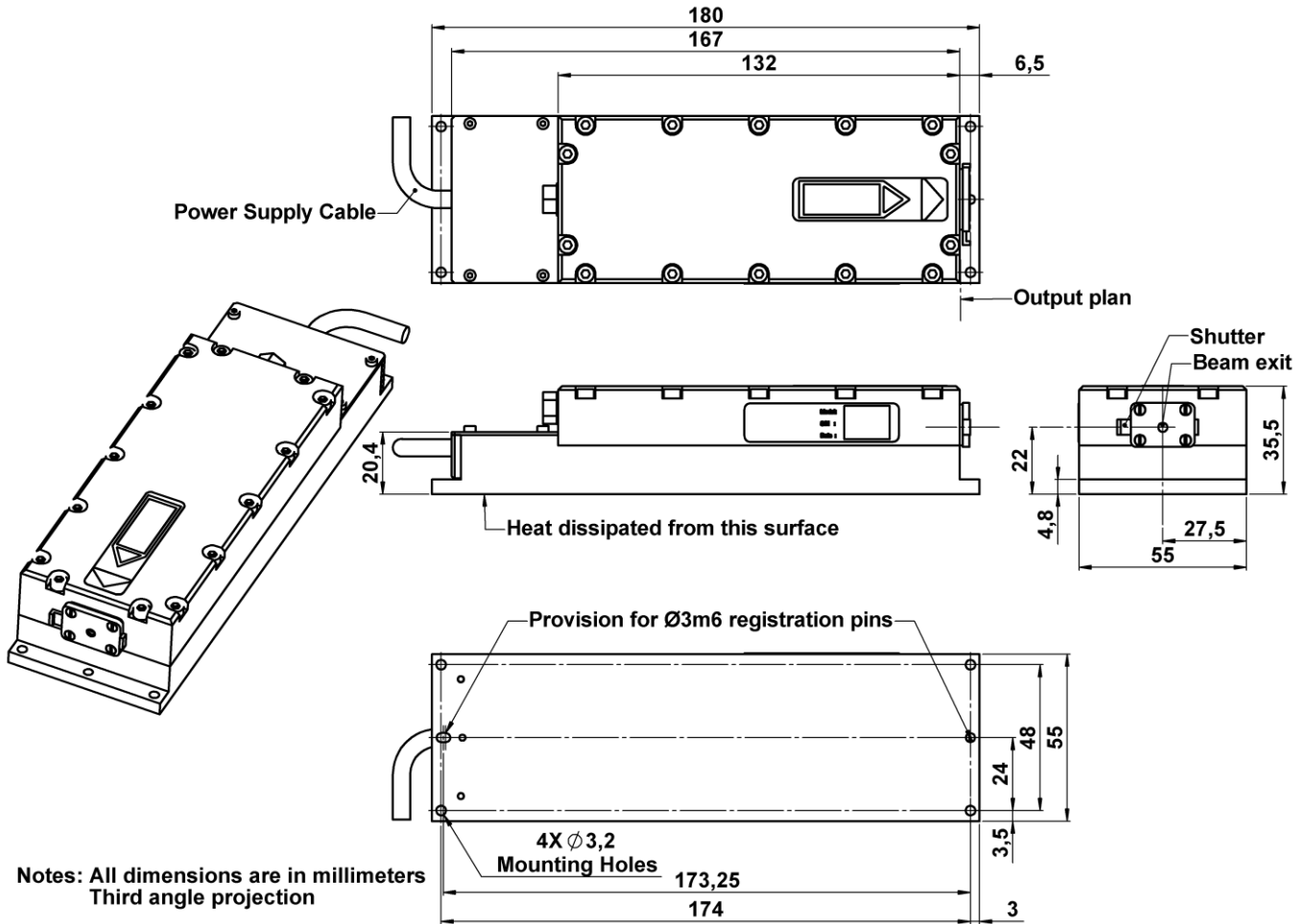
Environment Parameters	
Operating Temperature Range	15-35°C
Maximum Laser Head Baseplate Temperature	<50°C
Maximum Power Consumption	<40W
Laser Head Thermal Dissipation	<15W
Storage Temperature	0-50°C
Shock of 11ms according to IEC 68-2-27, non operating	25g
Vibration 5Hz to 500Hz sinusoidal according to IEC 68-2-6	2g

Certification	
Laser classification according to IEC 60825-1:2007	3B for SNV lasers 4 for SNU-02P and SNU-20F
CDRH	Yes, if used with a -DR1 controller
ROHs	Yes

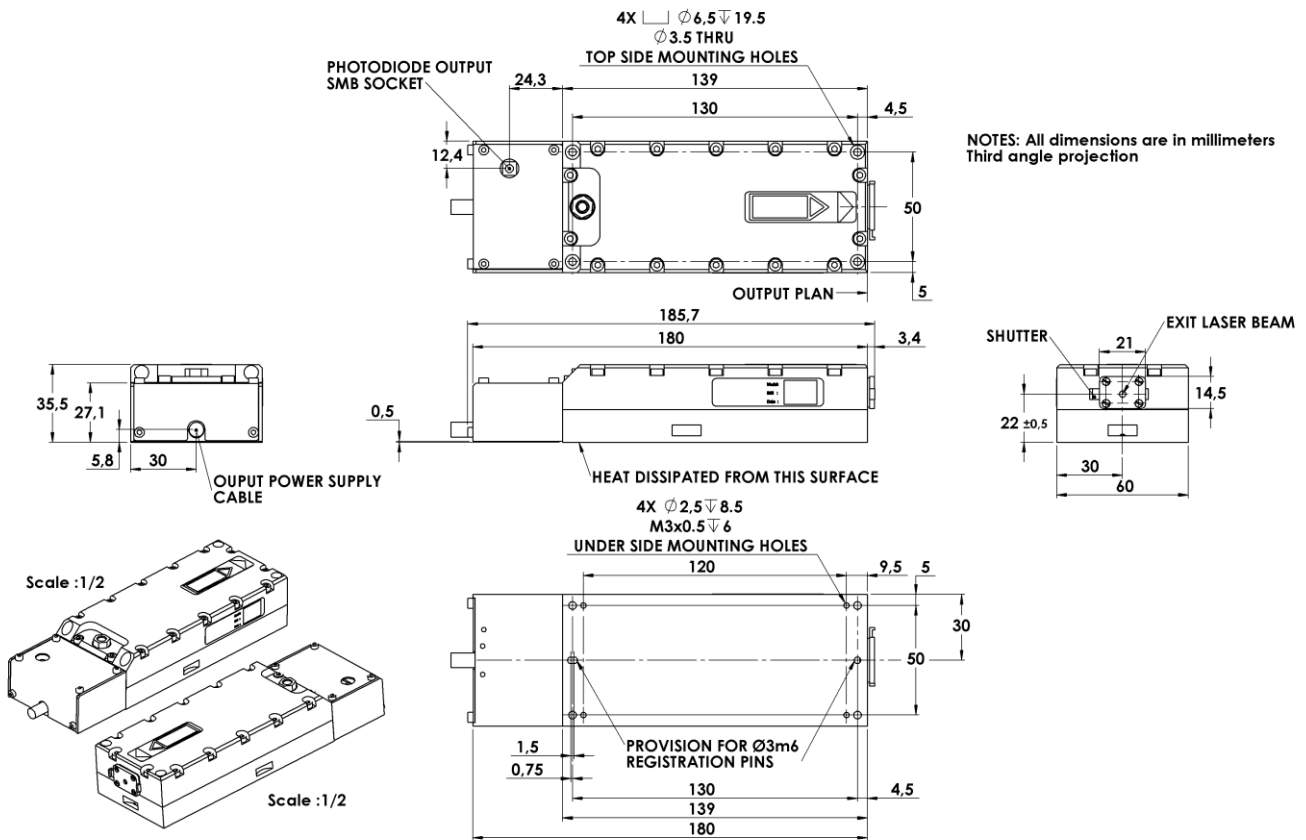
Options	
Collimation (C)	With collimated beam
Synchronization output (S)	TTL compatible output signal for synchronization/monitoring

Available Controller Types				
Model for the SNV-60-100 laser	Model for the other SNV and SNU lasers	Type	Input Power	CDRH
MLC-05A-DR1	MLC-03A-DR1	Desktop	100-240 V AC	Yes
MLC-05A-MR1	MLC-03A-MR1	Module	12 V DC	No
MLC-05A-BR1	MLC-03A-BR1	Board	12 V DC	No

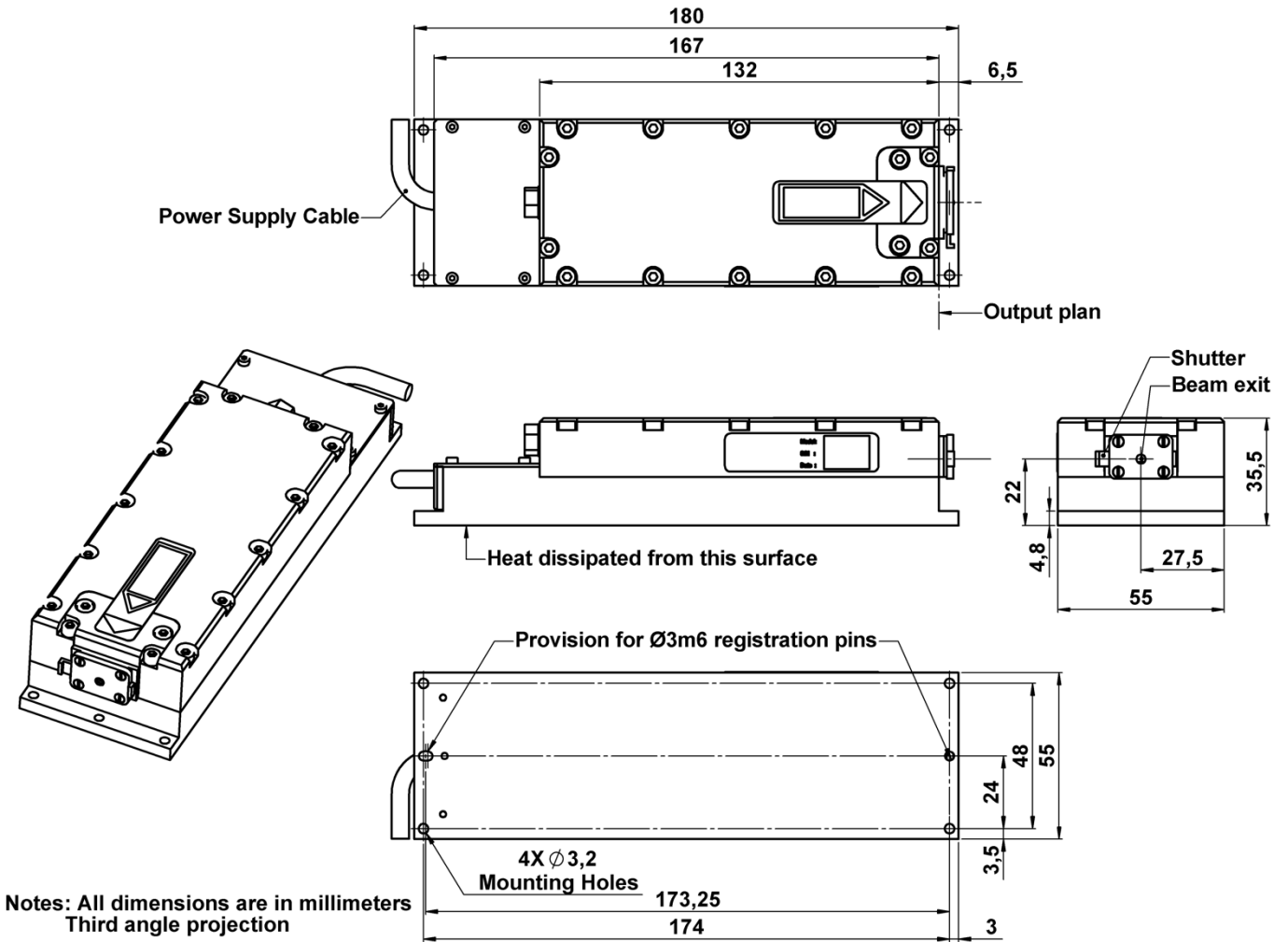
CDRH LASER HEAD MECHANICAL DRAWINGS: SNV-05P-100



CDRH LASER HEAD MECHANICAL DRAWINGS: SNV-20F-100, SNV-40P-100 & SNV-60P-100



CDRH LASER HEAD MECHANICAL DRAWINGS: SNU-02P-100



CDRH LASER HEAD MECHANICAL DRAWINGS: SNU-20F-100

